Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- MLPAK33 package (3.3 x 3.3 mm footprint)

3. Applications

- High-side load switch
- Battery management
- DC-to-DC conversion
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V	
V_{GS}	gate-source voltage			-25	-	25	V	
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-22.1	Α	
Static charact	Static characteristics							
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -13.4 A; T_j = 25 °C		-	5	6.1	mΩ	
	resistance	V_{GS} = -4.5 V; I_D = -11.7 A; T_j = 25 °C		-	6.4	8.1	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source		D
4	G	gate]	
5	D	drain		
6	D	drain	المممكا	S 017aaa257
7	D	drain	8 7 6 5	
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PXP6R1-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1		

7. Marking

Table 4. Marking codes

Type number	Marking code
PXP6R1-30QL	7AC

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-25	25	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-22.1	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-13.5	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-8.5	Α
		V _{GS} = -10 V; T _{sp} = 25 °C		-	-71.1	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-123	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	4.8	W
		T _{amb} = 25 °C	[1]	-	1.8	W
		T _{sp} = 25 °C		-	50	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode		'	'		
Is	source current	T _{amb} = 25 °C	[1]	-	-1.7	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

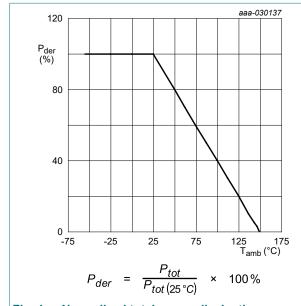


Fig. 1. Normalized total power dissipation as a function of ambient temperature

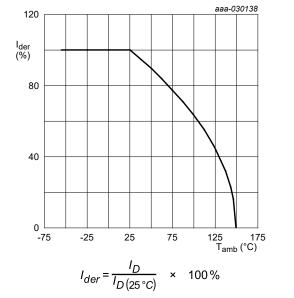


Fig. 2. Normalized continous drain current as a function of ambient temperature

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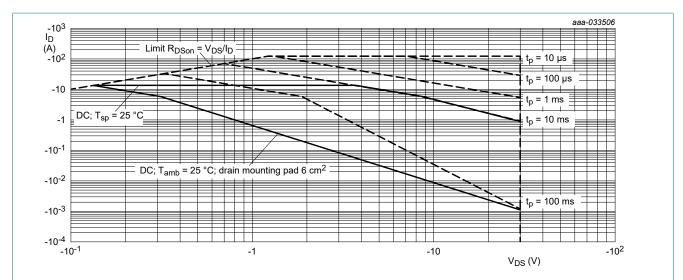


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

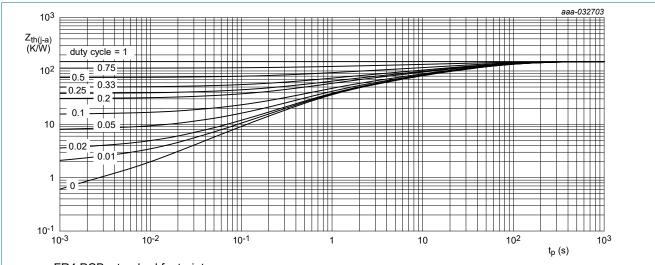
30 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

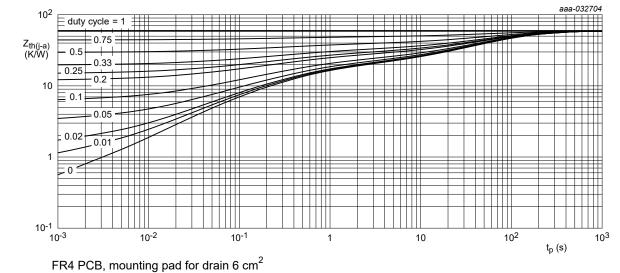
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	in free air [[1]	-	145	185	K/W	
	junction to ambient		[2]	-	55	70	K/W
		in free air; t ≤ 5 s	[2]	-	21	26	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	1.5	2.5	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-1.5	-2	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -13.4 A; T_j = 25 °C	-	5	6.1	mΩ
	resistance	$V_{GS} = -10 \text{ V}; I_D = -13.4 \text{ A}; T_j = 150 \text{ °C}$	-	8.1	9.9	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -11.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	6.4	8.1	mΩ
9fs	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -13.4 \text{ A}; T_j = 25 \text{ °C}$	-	50	-	S
R_G	gate resistance	f = 1 MHz	-	5.8	-	Ω
Dynamic ch	naracteristics					,
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -13.4 A; V_{GS} = -10 V; T_{j} = 25 °C	-	77.8	116.7	nC
		V _{DS} = -15 V; I _D = -11.7 A; V _{GS} = -4.5 V;	-	38.2	57.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	8.6	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	3.2	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	5.4	-	nC
Q_{GD}	gate-drain charge		-	14.5	-	nC
V_{GSpl}	gate-source plateau voltage	V_{DS} = -15 V; I_D = -11.7 A; T_j = 25 °C	-	-2.4	-	V
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	3800	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	460	-	pF
C _{rss}	reverse transfer capacitance		-	390	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -15 V; I _D = -11.7 A; V _{GS} = -4.5 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$; $T_j = 25 °C$	-	62	-	ns
t _{d(off)}	turn-off delay time		-	68	-	ns
t _f	fall time	1	-	52	-	ns
Source-dra	in diode		ı		<u>'</u>	1
V _{SD}	source-drain voltage	$I_S = -1.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.6	-1.2	V
t _{rr}	reverse recovery time	I _S = -1.7 A; dI _S /dt = 100 A/μs;	-	24	-	ns
Q _r	recovered charge	V _{GS} = -4.5 V; V _{DS} = -15 V; T _j = 25 °C	-	14	-	nC
t _a	reverse recovery rise time		-	12	-	ns
t _b	reverse recovery fall time		-	12	-	ns

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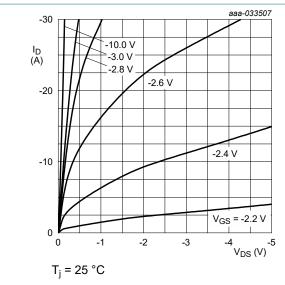


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

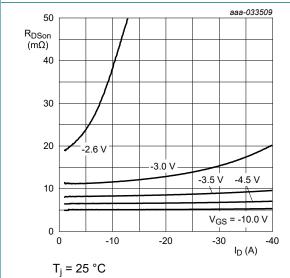


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

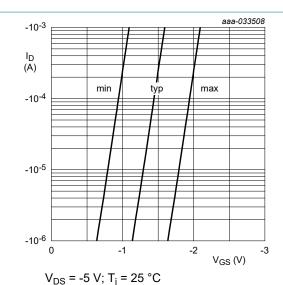


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

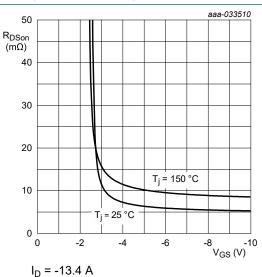


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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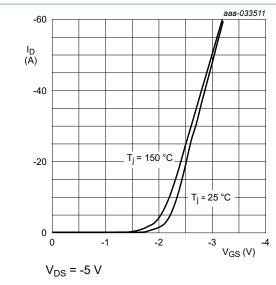


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

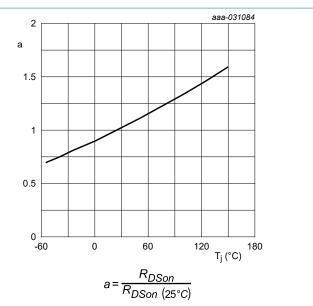


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature; typical values

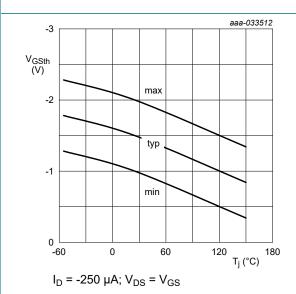


Fig. 12. Gate-source threshold voltage as a function of junction temperature

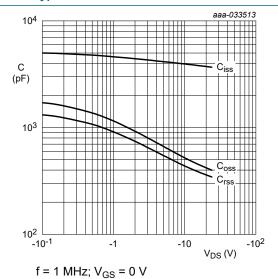


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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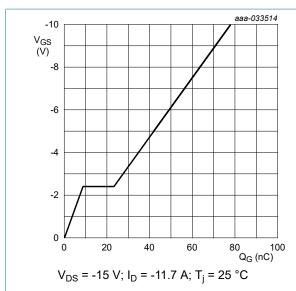


Fig. 14. Gate-source voltage as a function of gate charge; typical values

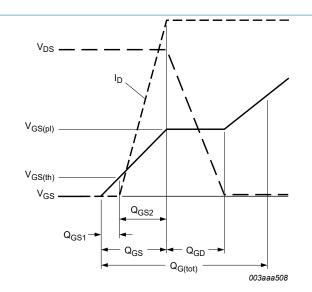


Fig. 15. Gate charge waveform definitions

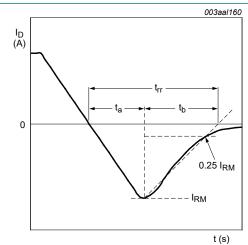


Fig. 16. Reverse recovery timing definition

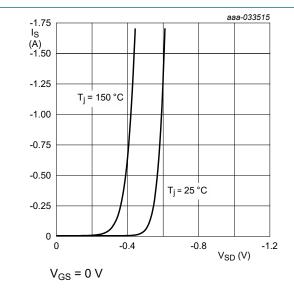
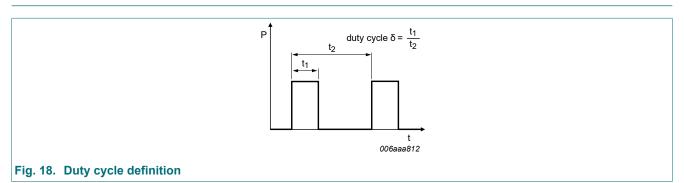


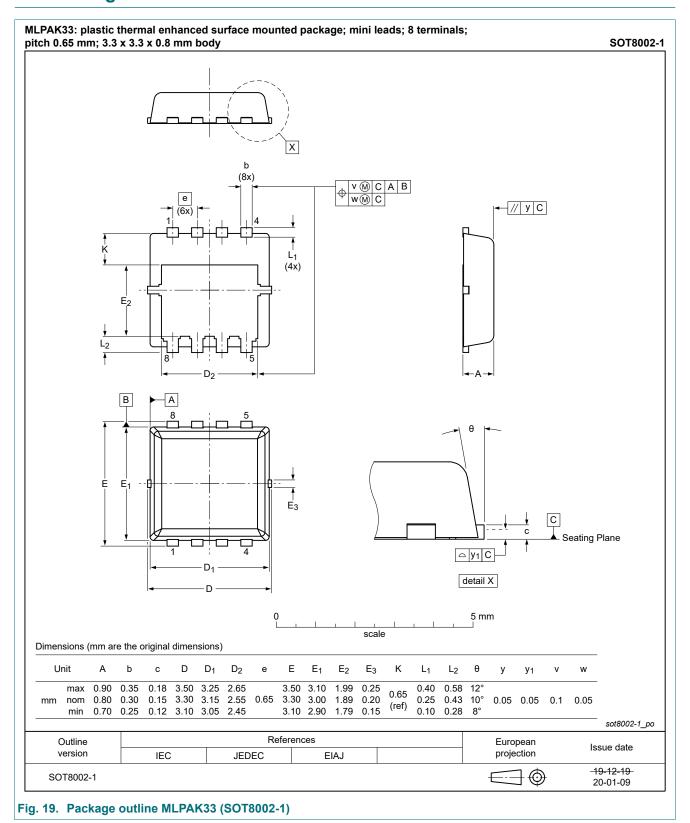
Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information



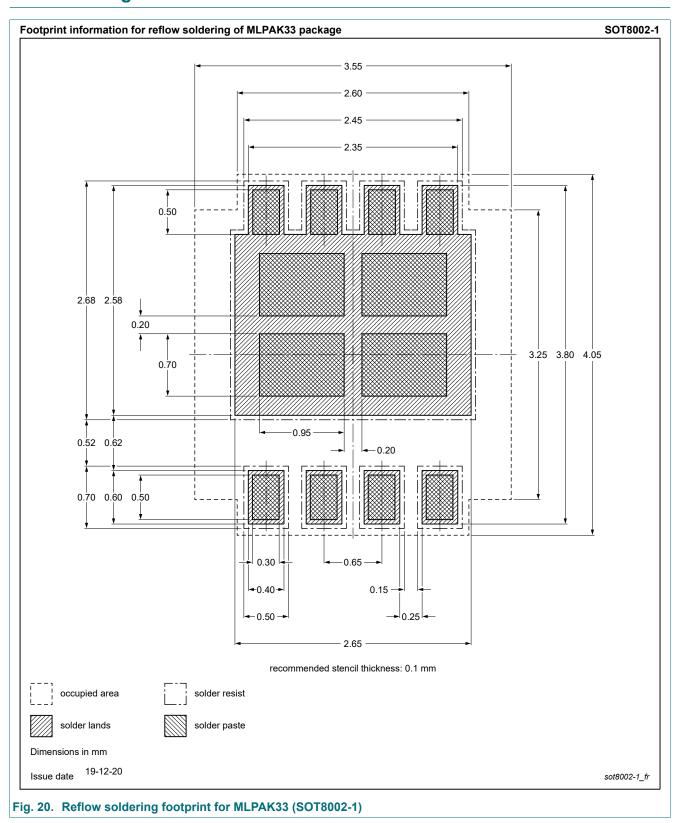
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12. Package outline



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13. Soldering



30 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXP6R1-30QL v.1	20210906	Product data sheet	-	-

30 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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